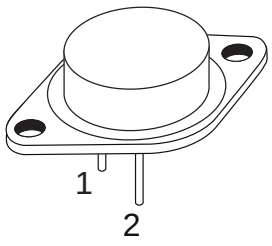
BUR51

HIGH CURRENT NPN SILICON TRANSISTOR

- STMicroelectronics PREFERRED SALESTYPE
- NPN TRANSISTOR

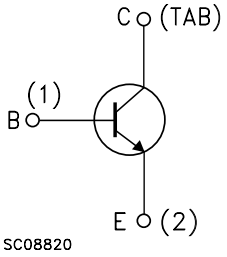
DESCRIPTION

The BUR51 is a silicon Multiepitaxial Planar NPN transistor in modified Jedec TO-3 metal case, intented for use in switching and linear applications in military and industrial equipment.



TO-3

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage (I_E = 0)	300	V
V_{CEO}	Collector-Emitter Voltage (I_B = 0)	200	V
V_{EBO}	Emitter-Base Voltage (I_C = 0)	10	V
I_C	Collector Current	60	A
I_{CM}	Collector Peak Current (t_p = 10 ms)	80	A
I_B	Base Current	16	A
P_{tot}	Total Dissipation at $T_c \leq 25\ ^oC$	350	W
T_{stg}	Storage Temperature	-65 to 200	^oC
T_j	Max. Operating Junction Temperature	200	^oC

THERMAL DATA

$R_{thj\text{-}case}$	Thermal Resistance Junction-case	Max	0.5	$^oC/W$

ELECTRICAL CHARACTERISTICS (T_{case} = 25 ^oC unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector Cut-off Current (I_E = 0)	V_{CB} = 300 V V_{CB} = 300 V T_c = 125 ^oC			0.2 2	mA mA
I_{CEO}	Collector Cut-off Current (I_B = 0)	V_{CE} =200 V			1	mA
I_{EBO}	Emitter Cut-off Current (I_C = 0)	V_{EB} = 7 V			0.2	µA
$V_{CEO(sus)}$*	Collector-Emitter Sustaining Voltage (I_B = 0)	I_C = 200 mA	200			V
V_{EBO}	Emitter-base Voltage (I_C = 0)	I_E = 10 mA	10			V
$V_{CE(sat)}$*	Collector-emitter Saturation Voltage	I_C = 30 A I_B = 2 A I_C = 50 A I_B = 5 A		 0.9	1 1.5	V V
$V_{BE(sat)}$*	Base-emitter Saturation Voltage	I_C = 30 A I_B = 2 A I_C = 50 A I_B = 5 A		 1.55	1.8 2	V V
h_{FE}*	DC Current Gain	I_C = 5 A V_{CE} = 4 V I_C = 50 A V_{CE} = 4 V	20 15		100	
$I_{s/b}$	Second Breakdown Collector Current	V_{CE} = 20 V t = 1 s	17.5			A
f_T	Transition-Frequency	I_C = 1 A V_{CE} = 5 V f = 1 MHz	10	16		MHz
t_{on}	Turn-on Time	I_C = 50 A I_{B1} = 5 A V_{CC} = 100 V		0.35	1	µs
t_s t_f	Storage Time Fall Time	I_C = 50 A I_{B1} = 5 A I_{B2} = -5 A V_{CC} = 100 V		0.9 0.24	2 0.6	µs µs
	Clamped $E_{s/b}$ Collector Current	V_{clamp} = 200 V L = 500 µH	50			A

* Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %

TO-3 (I) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	11	11.7	13.1	0.433	0.461	0.516
B	1.45	1.5	1.6	0.057	0.059	0.063
C	2.7		2.92	0.106		0.115
D	8.9		9.4	0.350		0.370
E	19		20	0.748		0.787
G	10.7	10.9	11.1	0.421	0.429	0.437
N	16.5	16.9	17.2	0.650	0.665	0.677
P	25		26	0.984		1.024
R	3.88		4.2	0.153		0.165
U	38.5		39.3	1.516		1.547
V	30	30.14	30.3	1.181	1.187	1.193